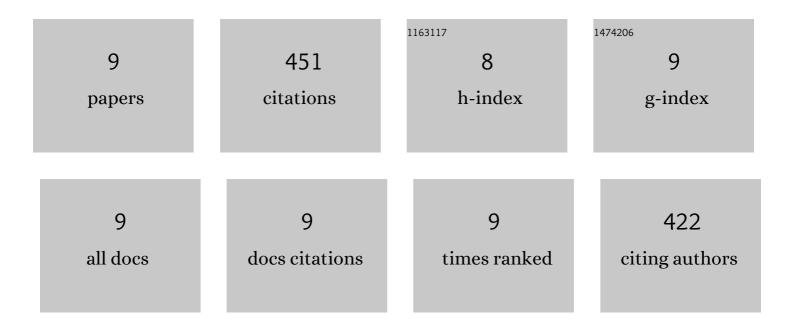
## Hongpo Hu

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Boosted ultraviolet electroluminescence of InGaN/AlGaN quantum structures grown on high-index contrast patterned sapphire with silica array. Nano Energy, 2020, 69, 104427.	16.0	150
2	Effects of GaN/AlGaN/Sputtered AlN nucleation layers on performance of GaN-based ultraviolet light-emitting diodes. Scientific Reports, 2017, 7, 44627.	3.3	92
3	High quality GaN buffer layer by isoelectronic doping and its application to 365â€ <sup>-</sup> nm InGaN/AlGaN ultraviolet light-emitting diodes. Applied Surface Science, 2019, 471, 231-238.	6.1	76
4	Growth of high-quality AlN films on sapphire substrate by introducing voids through growth-mode modification. Applied Surface Science, 2020, 518, 146218.	6.1	43
5	Effect of strain relaxation on performance of InGaN/GaN green LEDs grown on 4-inch sapphire substrate with sputtered AlN nucleation layer. Scientific Reports, 2019, 9, 3447.	3.3	42
6	Strain management and AlN crystal quality improvement with an alternating V/III ratio AlN superlattice. Applied Physics Letters, 2021, 118, .	3.3	19
7	Heteroepitaxial Growth of High-Quality and Crack-Free AlN Film on Sapphire Substrate with Nanometer-Scale-Thick AlN Nucleation Layer for AlGaN-Based Deep Ultraviolet Light-Emitting Diodes. Nanomaterials, 2019, 9, 1634.	4.1	12
8	Strategically constructed patterned sapphire with silica array to boost substrate performance in GaN-based flip-chip visible light-emitting diodes. Optics Express, 2020, 28, 38444.	3.4	12
9	A Comparative Study of GaNâ€Based Direct Current and Alternating Current High Voltage Lightâ€Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700554.	1.8	5